

In the Claims

Claims 1-35 are canceled.

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36. [Amended] A semiconductor workpiece processing method comprising:
providing a semiconductor process chamber;
supplying slurry to the semiconductor process chamber; and
monitoring the turbidity of the slurry during the supplying using a sensor.

what does sensor monitor turbidity of

37. [Original] The method according to claim 36 wherein the supplying comprises using a supply connection and the monitoring comprises monitoring slurry within the supply connection.

or slurry supply

38. [Original] The method according to claim 37 further comprising coupling the sensor with the supply connection.

or both

39. [Original] The method according to claim 36 wherein the monitoring comprises:

emitting electromagnetic energy towards the slurry; and
receiving at least some of the electromagnetic energy.

40. [Original] The method according to claim 36 further comprising generating a signal indicative of the turbidity after the monitoring.

41. [Original] The method according to claim 36 further comprising insulating the slurry from the sensor.

42. [Original] The method according to claim 36 wherein the providing comprises providing a chemical-mechanical polishing process chamber.

Claims 43-52 are canceled.

53. [Original] A semiconductor workpiece processing method comprising:
providing a semiconductor processor having a process chamber configured to receive a semiconductor workpiece;
supplying slurry to the process chamber using a connection;
emitting electromagnetic energy towards the connection using a sensor;
receiving at least some of the electromagnetic energy using the sensor; and
generating a signal indicative of turbidity of the slurry responsive to the receiving.

54. [Original] The method according to claim 53 wherein the emitting comprises emitting infrared electromagnetic energy.

55. [Original] The method according to claim 53 further comprising substantially insulating the slurry from the sensor.

56. [Original] The method according to claim 53 wherein the providing comprises providing chemical-mechanical polishing semiconductor processor.

57. [Original] The method according to claim 53 further comprising attaching the sensor to the connection and detaching the sensor from the connection while maintaining the supplying.

58. [Original] A semiconductor workpiece processing method comprising:

- providing a semiconductor processor having a process chamber configured to receive a semiconductor workpiece;
- supplying slurry to the process chamber using a connection;
- emitting infrared electromagnetic energy using a source;
- splitting the infrared electromagnetic energy to direct some of the infrared electromagnetic energy towards the connection;
- first receiving at least some of the infrared electromagnetic energy passing through the connection using a first receiver;
- generating a feedback signal using the first receiver responsive to the first receiving;
- adjusting the emitting via the source responsive to the feedback signal to provide a substantially constant amount of electromagnetic energy to the first receiver;
- second receiving at least some of the infrared electromagnetic energy not passing through the connection using a second receiver; and
- generating a signal indicative of turbidity of the slurry using the second receiver responsive to the second receiving.

59. [New] The method according to claim 36 further comprising providing the slurry and the monitoring comprises monitoring after the providing.

60. [New] The method according to claim 37 wherein the supply connection is configured to supply the slurry in at least a partially horizontal direction.